Sanjay Krishna

List of Publications by Year
in descending order

509 papers	10,367 citations	38720 50 h-index	54882 84 g-index
514 all docs	514 docs citations	514 times ranked	7127 citing authors

#	Article	IF	Citations
1	Terahertz compressive imaging with metamaterial spatial light modulators. Nature Photonics, 2014, 8, 605-609.	15.6	676
2	Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors. Nature, 2010, 468, 286-289.	13.7	373
3	A Surface Plasmon Enhanced Infrared Photodetector Based on InAs Quantum Dots. Nano Letters, 2010, 10, 1704-1709.	4.5	277
4	n B n structure based on InAsâˆ•GaSb type-II strained layer superlattices. Applied Physics Letters, 2007, 91, .	1.5	217
5	Quantum dots-in-a-well infrared photodetectors. Journal Physics D: Applied Physics, 2005, 38, 2142-2150.	1.3	200
6	Normal-incidence, high-temperature, mid-infrared, InAs-GaAs vertical quantum-dot infrared photodetector. IEEE Journal of Quantum Electronics, 2001, 37, 1412-1419.	1.0	167
7	A multispectral and polarization-selective surface-plasmon resonant midinfrared detector. Applied Physics Letters, 2009, 95, .	1.5	165
8	Cavity Q, mode volume, and lasing threshold in small diameter AlGaAs microdisks with embedded quantum dots. Optics Express, 2006, 14, 1094.	1.7	151
9	High-responsivity, normal-incidence long-wave infrared (Î»âˆ¼7.2â€‰Î¼m) InAs/In0.15Ga0.85As dots-in-a-well detector. Applied Physics Letters, 2002, 81, 1369-1371.	1.5	145
10	Absorption, carrier lifetime, and gain in inas~gaas quantum-dot infrared photodetectors. IEEE Journal of Quantum Electronics, 2003, 39, 459-467.	1.0	145
11	Second Harmonic Generation from a Nanopatterned Isotropic Nonlinear Material. Nano Letters, 2006, 6, 1027-1030.	4.5	140
12	A monolithically integrated plasmonic infrared quantum dot camera. Nature Communications, 2011, 2, 286.	5.8	137
13	Demonstration of a 320Ã—256 two-color focal plane array using InAs/InGaAs quantum dots in well detectors. Applied Physics Letters, 2005, 86, 193501.	1.5	131
14	Performance improvement of longwave infrared photodetector based on type-II InAs/GaSb superlattices using unipolar current blocking layers. Applied Physics Letters, 2010, 96, .	1.5	121
15	High-detectivity, normal-incidence, mid-infrared (Î»âˆ¼4â€ŠÎ¼m)InAs/GaAs quantum-dot detector operating at 150 K. Applied Physics Letters, 2001, 79, 421-423.	1.5	114
16	Quantum dot infrared photodetector enhanced by surface plasma wave excitation. Optics Express, 2009, 17, 23160.	1.7	114
17	Phonon-polaritonics: enabling powerful capabilities for infrared photonics. Nanophotonics, 2019, 8, 2129-2175.	2.9	113
18	Three-color (Î»p1âˆ¼3.8â€,Î¼m, Î»p2âˆ¼8.5â€,Î¼m, and Î»p3âˆ¼23.2â€,Î¼m) InAs/InGaAs quantum-dots-in-a-well detector. Applied Physics Letters, 2003, 83, 2745-2747.	1.5	110

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19	Review of current progress in quantum dot infrared photodetectors. Laser and Photonics Reviews, 2010, 4, 738-750.	4.4	110
20	Quantum Confinement Effects in Nanoscale-Thickness InAs Membranes. Nano Letters, 2011, 11, 5008-5012.	4.5	97
21	A molecular phylogeny of ichthyophiid caecilians (Amphibia: Gymnophiona: Ichthyophiidae): out of India or out of South East Asia?. Proceedings of the Royal Society B: Biological Sciences, 2002, 269, 1563-1569.	1.2	94
22	High operating temperature interband cascade midwave infrared detector based on type-II InAs/GaSb strained layer superlattice. Applied Physics Letters, 2012, 101, .	1.5	93
23	Nanoscale quantum dot infrared sensors with photonic crystal cavity. Applied Physics Letters, 2006, 88, 151104.	1.5	92
24	640$,imes,$512 Pixels Long-Wavelength Infrared (LWIR) Quantum-Dot Infrared Photodetector (QDIP) Imaging Focal Plane Array. IEEE Journal of Quantum Electronics, 2007, 43, 230-237.	1.0	87
25	High-speed modulation and switching characteristics of In(Ga)As-Al(Ga)As self-organized quantum-dot lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 426-438.	1.9	86
26	Nanoscale InGaSb Heterostructure Membranes on Si Substrates for High Hole Mobility Transistors. Nano Letters, 2012, 12, 2060-2066.	4.5	85
27	Fourâ€Color Metamaterial Absorber THz Spatial Light Modulator. Advanced Optical Materials, 2013, 1, 905-909.	3.6	84
28	IIIâ€"V Complementary Metalâ€"Oxideâ€"Semiconductor Electronics on Silicon Substrates. Nano Letters, 2012, 12, 3592-3595.	4.5	80
29	Self-organized In0.4Ga0.6As quantum-dot lasers grown on Si substrates. Applied Physics Letters, 1999, 74, 1355-1357.	1.5	79
30	Mid-IR focal plane array based on type-II InAsâˆ•GaSb strain layer superlattice detector with nBn design. Applied Physics Letters, 2008, 92, .	1.5	78
31	Theoretical modeling and experimental characterization of InAsâˆ•InGaAs quantum dots in a well detector. Journal of Applied Physics, 2004, 96, 3782-3786.	1.1	77
32	Optical loss and lasing characteristics of high-quality-factor AlGaAs microdisk resonators with embedded quantum dots. Applied Physics Letters, 2005, 86, 151106.	1.5	77
33	Ultrathin body InAs tunneling field-effect transistors on Si substrates. Applied Physics Letters, 2011, 98, .	1.5	76
34	Quantum of optical absorption in two-dimensional semiconductors. Proceedings of the National Academy of Sciences of the United States of America, 2013, 110, 11688-11691.	3.3	75
35	Self-Aligned, Extremely High Frequency IIIâ€"V Metal-Oxide-Semiconductor Field-Effect Transistors on Rigid and Flexible Substrates. Nano Letters, 2012, 12, 4140-4145.	4.5	73
36	Multi-stack InAs/InGaAs sub-monolayer quantum dots infrared photodetectors. Applied Physics Letters, 2013, 102, 011131.	1.5	73

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37	Bias dependent dual band response from InAsâˆ•Ga(In)Sb type II strain layer superlattice detectors. Applied Physics Letters, 2007, 91, .	1.5	72
38	Two color InAs/InGaAs dots-in-a-well detector with background-limited performance at 91 K. Applied Physics Letters, 2003, 82, 2574-2576.	1.5	71
39	Spectrally adaptive infrared photodetectors with bias-tunable quantum dots. Journal of the Optical Society of America B: Optical Physics, 2004, 21, 7.	0.9	66
40	Ultra-thin infrared metamaterial detector for multicolor imaging applications. Optics Express, 2017, 25, 23343.	1.7	66
41	Normal-incidence InAs/In0.15Ga0.85As quantum dots-in-a-well detector operating in the long-wave infrared atmospheric window (8â€“12 Î¼m). Journal of Applied Physics, 2004, 96, 1036-1039.	1.1	64
42	Modeling of electrical characteristics of midwave type II InAsâˆ•GaSb strain layer superlattice diodes. Journal of Applied Physics, 2008, 104, .	1.1	60
43	Quantum dots-in-a-well infrared photodetectors. Infrared Physics and Technology, 2005, 47, 153-163.	1.3	57
44	Quantum Dot Based Infrared Focal Plane Arrays. Proceedings of the IEEE, 2007, 95, 1838-1852.	16.4	57
45	Mid-infrared InAs/GaSb strained layer superlattice detectors with nBn design grown on a GaAs substrate. Semiconductor Science and Technology, 2010, 25, 085010.	1.0	56
46	InAs/InAsSb strain balanced superlattices for optical detectors: Material properties and energy band simulations. Journal of Applied Physics, 2012, 111, 034507.	1.1	54
47	Midwave infrared type-II InAsâˆ•GaSb superlattice detectors with mixed interfaces. Journal of Applied Physics, 2006, 100, 014510.	1.1	53
48	Light direction-dependent plasmonic enhancement in quantum dot infrared photodetectors. Applied Physics Letters, 2010, 97, .	1.5	52
49	Varshni parameters for InAs/GaSb strained layer superlattice infrared photodetectors. Journal Physics D: Applied Physics, 2011, 44, 075102.	1.3	52
50	Mid-infrared InAs0.79Sb0.21-based <i>nBn</i> photodetectors with Al0.9Ga0.2As0.1Sb0.9 barrier layers, and comparisons with InAs0.87Sb0.13â€ˆ<i>p-i-n</i> diodes, both grown on GaAs using interfacial misfit arrays. Applied Physics Letters, 2013, 103, .	1.5	50
51	Sub-monolayer quantum dots in confinement enhanced dots-in-a-well heterostructure. Applied Physics Letters, 2012, 100, .	1.5	49
52	Assessment of quantum dot infrared photodetectors for high temperature operation. Journal of Applied Physics, 2008, 104, 034314.	1.1	47
53	Effect of well width on three-color quantum dots-in-a-well infrared detectors. IEEE Photonics Technology Letters, 2005, 17, 1064-1066.	1.3	46
54	Type II InAsâˆ•GaSb strain layer superlattice detectors with p-on-n polarity. Applied Physics Letters, 2007, 91, 133512.	1.5	46

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55	Low-strain InAsâˆ•InGaAsâˆ•GaAs quantum dots-in-a-well infrared photodetector. Journal of Vacuum Science & Technology B, 2008, 26, 1136.	1.3	46
56	Performance improvement of InAs/GaSb strained layer superlattice detectors by reducing surface leakage currents with SU-8 passivation. Applied Physics Letters, 2010, 96, 033502.	1.5	46
57	Design of plasmonic photonic crystal resonant cavities for polarization sensitive infrared photodetectors. Optics Express, 2010, 18, 3672.	1.7	46
58	InAsSb-Based Infrared Photodetectors: Thirty Years Later On. Sensors, 2020, 20, 7047.	2.1	46
59	Reduction of surface leakage current in InAs/GaSb strained layer long wavelength superlattice detectors using SU-8 passivation. Applied Physics Letters, 2010, 97, .	1.5	44
60	InAs/GaAs <i>p</i>-type quantum dot infrared photodetector with higher efficiency. Applied Physics Letters, 2013, 103, .	1.5	43
61	Structural and luminescence characteristics of cycled submonolayer InAs/GaAs quantum dots with room-temperature emission at 1.3 Î¼m. Journal of Applied Physics, 1999, 86, 6135-6138.	1.1	42
62	Single bump, two-color quantum dot camera. Applied Physics Letters, 2007, 91, 081120.	1.5	42
63	Passivation techniques for InAs/GaSb strained layer superlattice detectors. Laser and Photonics Reviews, 2013, 7, 45-59.	4.4	42
64	Detection theory for accurate and non-invasive skin cancer diagnosis using dynamic thermal imaging. Biomedical Optics Express, 2017, 8, 2301.	1.5	42
65	Room-Temperature Optically Pumped (Al)GaSb Vertical-Cavity Surface-Emitting Laser Monolithically Grown on an Si(1 0 0) Substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1636-1641.	1.9	41
66	Resonant cavity enhanced InAsâˆ•In[sub 0.15]Ga[sub 0.85]As dots-in-a-well quantum dot infrared photodetector. Journal of Vacuum Science & Technology B, 2007, 25, 1186.	1.3	41
67	Lateral diffusion of minority carriers in InAsSb-based nBn detectors. Applied Physics Letters, 2010, 97, 123503.	1.5	41
68	Quantum Size Effects on the Chemical Sensing Performance of Two-Dimensional Semiconductors. Journal of Physical Chemistry C, 2012, 116, 9750-9754.	1.5	41
69	Benchmarking the performance of ultrathin body InAs-on-insulator transistors as a function of body thickness. Applied Physics Letters, 2011, 99, .	1.5	40
70	Gallium free type II InAs/InAsxSb1-x superlattice photodetectors. Applied Physics Letters, 2012, 101, 071111.	1.5	40
71	Carrier lifetime studies in midwave infrared type-II InAs/GaSb strained layer superlattice. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	0.6	40
72	Low-bias, high-temperature performance of a normal-incidence InAs/GaAs vertical quantum-dot infrared photodetector with a current-blocking barrier. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1185.	1.6	39

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73	Electrochemical sulphur passivation of InAs/GaSb strain layer superlattice detectors. Electronics Letters, 2006, 42, 1248.	0.5	39
74	Dynamic infrared imaging for skin cancer screening. Infrared Physics and Technology, 2015, 70, 147-152.	1.3	38
75	Characterization of rapid-thermal-annealed InAs/In0.15Ga0.85As dots-in-well heterostructure using double crystal x-ray diffraction and photoluminescence. Applied Physics Letters, 2002, 80, 3898-3900.	1.5	37
76	Ultralow noise midwave infrared InAsâ€“GaSb strain layer superlattice avalanche photodiode. Applied Physics Letters, 2007, 91, 241111.	1.5	37
77	Bistability and self-pulsation in quantum-dot lasers with intracavity quantum-dot saturable absorbers. Applied Physics Letters, 1999, 74, 1654-1656.	1.5	36
78	Barrier Engineered Infrared Photodetectors Based on Type-II InAs/GaSb Strained Layer Superlattices. IEEE Journal of Quantum Electronics, 2013, 49, 211-217.	1.0	36
79	Systematic study of different transitions in high operating temperature quantum dots in a well photodetectors. Applied Physics Letters, 2010, 97, .	1.5	35
80	Demonstration of 640Ã—512 pixels long-wavelength infrared (LWIR) quantum dot infrared photodetector (QDIP) imaging focal plane array. Infrared Physics and Technology, 2007, 50, 149-155.	1.3	34
81	Canonical Correlation Feature Selection for Sensors With Overlapping Bands: Theory and Application. IEEE Transactions on Geoscience and Remote Sensing, 2008, 46, 3346-3358.	2.7	34
82	nBn detectors based on InAsâˆ•GaSb type-II strain layer superlattice. Journal of Vacuum Science & Technology B, 2008, 26, 1145-1148.	1.3	34
83	Optical properties of nonpolar III-nitrides for intersubband photodetectors. Journal of Applied Physics, 2013, 113, .	1.1	34
84	Vertical minority carrier electron transport in p-type InAs/GaSb type-II superlattices. Applied Physics Letters, 2012, 101, .	1.5	33
85	High quality interfaces of InAs-on-insulator field-effect transistors with ZrO2 gate dielectrics. Applied Physics Letters, 2013, 102, .	1.5	33
86	Room-temperature far-infrared emission from a self-organized InGaAs/GaAs quantum-dot laser. Applied Physics Letters, 2000, 76, 3355-3357.	1.5	32
87	Room-temperature optically-pumped GaSb quantum well based VCSEL monolithically grown on Si (100) substrate. Electronics Letters, 2006, 42, 350.	0.5	32
88	Bias-controlled wavelength switching in coupled-cavity In0.4Ga0.6As/GaAs self-organized quantum dot lasers. Applied Physics Letters, 1999, 74, 783-785.	1.5	31
89	Optical characterizations of heavily doped p-type AlxGa1âˆ’xAs and GaAs epitaxial films at terahertz frequencies. Journal of Applied Physics, 2005, 97, 093529.	1.1	31
90	InAs/GaSb Superlattice Detectors Operating at Room Temperature. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1269-1274.	1.9	31

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91	Reduction in dark current using resonant tunneling barriers in quantum dots-in-a-well long wavelength infrared photodetector. Applied Physics Letters, 2008, 93, 131115.	1.5	31
92	Passivation of long-wave infrared InAs/GaSb strained layer superlattice detectors. Infrared Physics and Technology, 2011, 54, 252-257.	1.3	31
93	Three color infrared detector using InAs/GaSb superlattices with unipolar barriers. Applied Physics Letters, 2011, 98, 121106.	1.5	31
94	AlInAsSb avalanche photodiodes on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	31
95	An electrically injected InAs/GaAs quantum-dot photonic crystal microcavity light-emitting diode. Applied Physics Letters, 2002, 81, 3876-3878.	1.5	30
96	Photoluminescence measurements of quantum-dot-containing semiconductor microdisk resonators using optical fiber taper waveguides. Physical Review B, 2005, 72, .	1.1	30
97	Optimization of InAs/GaSb type-II superlattice interfaces for long-wave (â^¼8Î¼m) infrared detection. Journal of Crystal Growth, 2009, 311, 1901-1904.	0.7	30
98	Radiation tolerance characterization of dual band InAs/GaSb type-II strain-layer superlattice pBp detectors using 63 MeV protons. Applied Physics Letters, 2012, 101, .	1.5	30
99	High operating temperature interband cascade focal plane arrays. Applied Physics Letters, 2014, 105, .	1.5	30
100	Low noise Al0.85Ga0.15As0.56Sb0.44 avalanche photodiodes on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	30
101	Confinement enhancing barriers for high performance quantum dots-in-a-well infrared detectors. Applied Physics Letters, 2011, 99, .	1.5	29
102	Theoretical investigation of quantum-dot avalanche photodiodes for mid-infrared applications. IEEE Journal of Quantum Electronics, 2005, 41, 1468-1473.	1.0	28
103	Influence of Si doping on the performance of quantum dots-in-well photodetectors. Journal of Vacuum Science & Technology B, 2006, 24, 1553.	1.3	28
104	High operating temperature split-off band infrared detectors. Applied Physics Letters, 2006, 89, 131118.	1.5	28
105	Demonstration of Bias-Controlled Algorithmic Tuning of Quantum Dots in a Well (DWELL) MidIR Detectors. IEEE Journal of Quantum Electronics, 2009, 45, 674-683.	1.0	28
106	Resonant Tunneling Barriers in Quantum Dots-in-a-Well Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2010, 46, 1105-1114.	1.0	28
107	Performance modeling of MWIR InAs/GaSb/Bâ€"Al0.2Ga0.8Sb type-II superlattice nBn detector. Semiconductor Science and Technology, 2012, 27, 055002.	1.0	28
108	Photovoltaic quantum dot quantum cascade infrared photodetector. Applied Physics Letters, 2012, 100, .	1.5	28

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109	Ultrathin-Body High-Mobility InAsSb-on-Insulator Field-Effect Transistors. IEEE Electron Device Letters, 2012, 33, 504-506.	2.2	28
110	Performance of mid-wave T2SL detectors with heterojunction barriers. Infrared Physics and Technology, 2013, 59, 22-27.	1.3	28
111	Mid-wavelength infrared type-II InAs/GaSb superlattice interband cascade photodetectors. Optical Engineering, 2014, 53, 043107.	0.5	28
112	Study of Short- and Long-Term Effectiveness of Ammonium Sulfide as Surface Passivation for InAs/GaSb Superlattices Using X-Ray Photoelectron Spectroscopy. Journal of Electronic Materials, 2010, 39, 2210-2214.	1.0	27
113	Long-Wave InAs/GaSb Superlattice Detectors Based on nBn and Pin Designs. IEEE Journal of Quantum Electronics, 2010, 46, 959-964.	1.0	27
114	Plasmonic-Enhanced Photodetectors for Focal Plane Arrays. IEEE Photonics Technology Letters, 2011, 23, 935-937.	1.3	27
115	Vertical carrier transport in strain-balanced InAs/InAsSb type-II superlattice material. Applied Physics Letters, 2020, 116, .	1.5	27
116	Long-wavelength infrared (LWIR) quantum-dot infrared photodetector (QDIP) focal plane array. , 2006, , .		26
117	Quantum Dots-in-a-Well Focal Plane Arrays. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1150-1161.	1.9	26
118	Electrical Characterization of Different Passivation Treatments for Long-Wave Infrared InAs/GaSb Strained Layer Superlattice Photodiodes. Journal of Electronic Materials, 2009, 38, 1944-1947.	1.0	26
119	Carrier dynamics in self-organized quantum dots and their application to long-wavelength sources and detectors. Journal of Crystal Growth, 2001, 227-228, 27-35.	0.7	25
120	Single quantum dot spectroscopy using a fiber taper waveguide near-field optic. Applied Physics Letters, 2007, 91, 091102.	1.5	25
121	QUANTUM DOT INFRARED DETECTORS AND SOURCES. International Journal of High Speed Electronics and Systems, 2002, 12, 969-994.	0.3	24
122	Transient photoconductivity measurements of carrier lifetimes in an InAsâˆ•In0.15Ga0.85As dots-in-a-well detector. Applied Physics Letters, 2007, 90, 103519.	1.5	24
123	Strain engineering of epitaxially transferred, ultrathin layers of III-V semiconductor on insulator. Applied Physics Letters, 2011, 98, 012111.	1.5	23
124	InAsSb-based<i>nBn</i>photodetectors: lattice mismatched growth on GaAs and low-frequency noise performance. Semiconductor Science and Technology, 2015, 30, 105011.	1.0	23
125	Frequency-division-multiplexed single-pixel imaging with metamaterials. Optica, 2016, 3, 133.	4.8	23
126	Room-temperature optically-pumped InGaSb quantum well lasers monolithically grown on Si(100) substrate. Electronics Letters, 2005, 41, 531.	0.5	22

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127	Statistical adaptive sensing by detectors with spectrally overlapping bands. Applied Optics, 2006, 45, 7224.	2.1	22
128	Lateral diffusion of minority carriers in nBn based type-II InAs/GaSb strained layer superlattice detectors. Applied Physics Letters, 2008, 93, 123507.	1.5	22
129	Noise, gain, and capture probability of p-type InAs-GaAs quantum-dot and quantum dot-in-well infrared photodetectors. Journal of Applied Physics, 2017, 121, 244501.	1.1	22
130	Background carrier concentration in midwave and longwave InAs/GaSb type II superlattices on GaAs substrate. Applied Physics Letters, 2010, 97, 051109.	1.5	21
131	High temperature operation of quantum dots-in-a-well infrared photodetectors. Infrared Physics and Technology, 2011, 54, 215-219.	1.3	21
132	Band engineered HOT midwave infrared detectors based on type-II InAs/GaSb strained layer superlattices. Infrared Physics and Technology, 2013, 59, 72-77.	1.3	21
133	Growth of high density self-organized (In,Ga)As quantum dots with ultranarrow photoluminescence linewidths using buried In(Ga,Al)As stressor dots. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1502.	1.6	20
134	Room-temperature long-wavelength (= 13.3 [micro sign]m) unipolar quantum dot intersubband laser. Electronics Letters, 2000, 36, 1550.	0.5	20
135	Intersubband gain and stimulated emission in long-wavelength (Î»=13 Î¼m) intersubband In(Ga)As-GaAs quantum-dot electroluminescent devices. IEEE Journal of Quantum Electronics, 2001, 37, 1066-1074.	1.0	20
136	Two-color focal plane arrays based on self assembled quantum dots in a well heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 439-443.	0.8	20
137	Midwavelength Infrared Avalanche Photodiode Using InAsâ€“GaSb Strain Layer Superlattice. IEEE Photonics Technology Letters, 2007, 19, 1843-1845.	1.3	20
138	Multispectral Quantum Dots-in-a-Well Infrared Detectors Using Plasmon Assisted Cavities. IEEE Journal of Quantum Electronics, 2010, 46, 1051-1057.	1.0	20
139	Investigation of multistack InAs/InGaAs/GaAs self-assembled quantum dots-in-double-well structures for infrared detectors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3G1-C3G7.	0.6	20
140	Bias Switchable Dual-Band InAs/GaSb Superlattice Detector With pBp Architecture. IEEE Photonics Journal, 2011, 3, 234-240.	1.0	20
141	nAnalysis of subwavelength metal hole array structure for the enhancement of back-illuminated quantum dot infrared photodetectors. Optics Express, 2013, 21, 4709.	1.7	20
142	n-Type GaAs/AlGaAs heterostructure detector with a 32 THz threshold frequency. Optics Letters, 2007, 32, 1335.	1.7	19
143	Ultrafast carrier dynamics in an InAs/InGaAs quantum dots-in-a-well heterostructure. Optics Express, 2008, 16, 1165.	1.7	19
144	Surface Charge Transfer Doping of IIIâ€“V Nanostructures. Journal of Physical Chemistry C, 2013, 117, 17845-17849.	1.5	19

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145	Structure of the first representative of Pfam family PF09410 (DUF2006) reveals a structural signature of the calycin superfamily that suggests a role in lipid metabolism. Acta Crystallographica Section F: Structural Biology Communications, 2010, 66, 1153-1159.	0.7	18
146	Photoluminescence study of InAs/InGaAs sub-monolayer quantum dot infrared photodetectors with various numbers of multiple stack layers. Journal of Luminescence, 2019, 207, 512-519.	1.5	18
147	Free carrier absorption in Be-doped epitaxial AlGaAs thin films. Applied Physics Letters, 2004, 85, 5236-5238.	1.5	17
148	The infrared retina. Journal Physics D: Applied Physics, 2009, 42, 234005.	1.3	17
149	Study of Surface Treatments on InAs/GaSb Superlattice LWIR Detectors. Journal of Electronic Materials, 2010, 39, 2203-2209.	1.0	17
150	Midwave infrared quantum dot avalanche photodiode. Applied Physics Letters, 2010, 97, .	1.5	17
151	Long-wave type-II superlattice detectors with unipolar electron and hole barriers. Optical Engineering, 2012, 51, 124001.	0.5	17
152	InAs/GaAs quantum dot and dots-in-well infrared photodetectors based on p -type valence-band intersublevel transitions. Infrared Physics and Technology, 2015, 70, 15-19.	1.3	17
153	Random alloy thick AlGaAsSb avalanche photodiodes on InP substrates. Applied Physics Letters, 2022, 120, .	1.5	17
154	High responsivity, LWIR dots-in-a-well quantum dot infrared photodetectors. Infrared Physics and Technology, 2003, 44, 517-526.	1.3	16
155	Characterization of carriers in GaSbâˆ•InAs superlattice grown on conductive GaSb substrate. Applied Physics Letters, 2008, 92, 012121.	1.5	16
156	Mid-wavelength InAsSb detectors based on nBn design. Proceedings of SPIE, 2010, , .	0.8	16
157	Versatile Spectral Imaging With an Algorithm-Based Spectrometer Using Highly Tuneable Quantum Dot Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2011, 47, 190-197.	1.0	16
158	Comparison of Quantum Dots-in-a-Double-Well and Quantum Dots-in-a-Well Focal Plane Arrays in the Long-Wave Infrared. IEEE Transactions on Electron Devices, 2011, 58, 2022-2027.	1.6	16
159	Quantum Dot Infrared Photodetectors. Semiconductors and Semimetals, 2011, 84, 153-193.	0.4	16
160	Growth of InAsâ€“InAsSb SLS through the use of digital alloys. Journal of Crystal Growth, 2015, 425, 29-32.	0.7	16
161	Single Pixel Quadrature Imaging with Metamaterials. Advanced Optical Materials, 2016, 4, 66-69.	3.6	16
162	Hot dot detectors. IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems, 2002, 18, 14-24.	0.8	15

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163	Effects of Si doping on normal incidence InAsâˆ•In0.15Ga0.85As dots-in-well quantum dot infrared photodetectors. Journal of Applied Physics, 2006, 99, 083105.	1.1	15
164	Electron barrier study of mid-wave infrared interband cascade photodetectors. Applied Physics Letters, 2013, 103, .	1.5	15
165	Modeling of midwavelength infrared InAs/GaSb type II superlattice detectors. Optical Engineering, 2013, 52, 061307.	0.5	15
166	Investigation of a near mid-gap trap energy level in mid-wavelength infrared InAs/GaSb type-II superlattices. Semiconductor Science and Technology, 2015, 30, 115004.	1.0	15
167	Antimonide-based membranes synthesis integration and strain engineering. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, E1-E8.	3.3	15
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